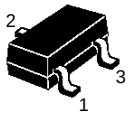
SGS-THOMSON MICROELECTRONICS

SOA56

SMALL SIGNAL PNP TRANSISTOR

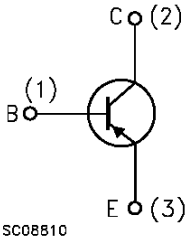
Type	Marking
SOA56	2GT

- SILICON EPITAXIAL PLANAR PNP TRANSISTORS
- MINIATURE PLASTIC PACKAGE FOR APPLICATION IN SURFACE MOUNTING CIRCUITS
- MEDIUM CURRENT AF AMPLIFICATION
- NPN COMPLEMENTS IS SOA06



SOT-23

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage (I_E = 0)	-80	V
V_{CEO}	Collector-Emitter Voltage (I_B = 0)	-80	V
V_{EBO}	Emitter-Base Voltage (I_C = 0)	-4	V
I_C	Collector Current	-0.5	A
P_{tot}	Total Dissipation at T_c = 25 °C	350	mW
T_{stg}	Storage Temperature	-65 to 150	°C
T_j	Max. Operating Junction Temperature	150	°C

THERMAL DATA

$R_{thj\text{-}amb}$ •	Thermal Resistance Junction-Ambient	Max	350	$^oC/W$

• Mounted on a ceramic substrate area = 15 x 15 x 0.5 mm

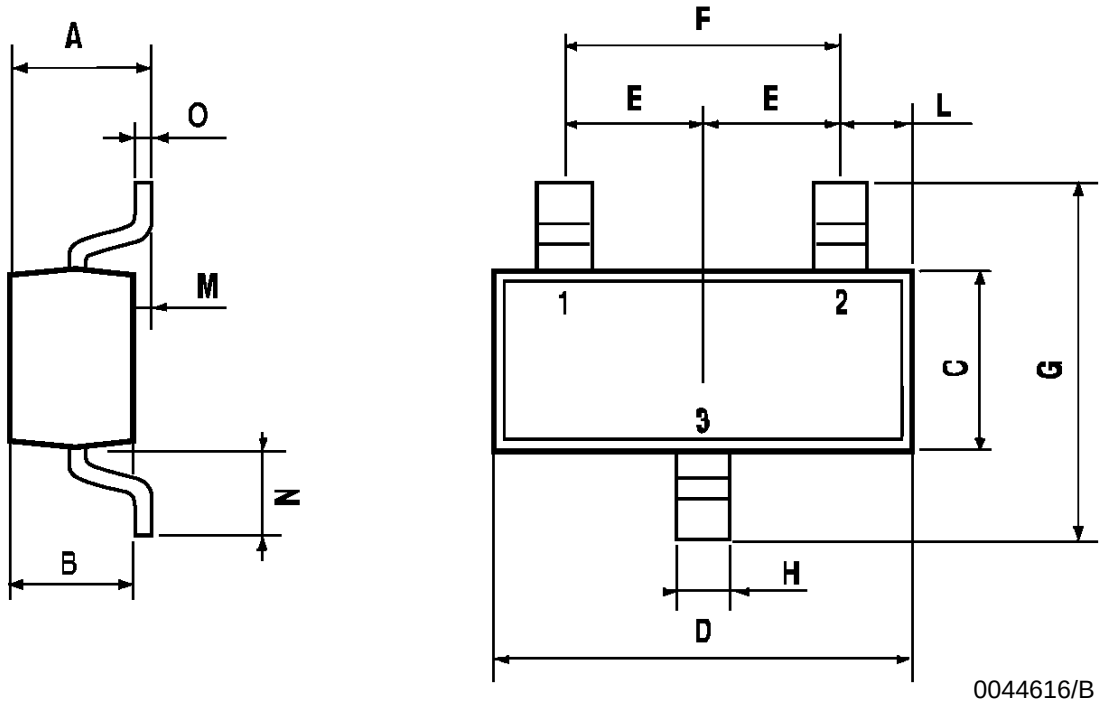
ELECTRICAL CHARACTERISTICS (T_{case} = 25 ^oC unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CBO}	Collector Cut-off Current (I_E = 0)	V_{CB} = -80 V			-100	nA
I_{CEO}	Collector Cut-off Current (I_E = 0)	V_{CE} = -60 V			-100	nA
$V_{(BR)CEO}$*	Collector-Emitter Breakdown Voltage (I_B = 0)	I_C = -1 mA	-80			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage (I_C = 0)	I_E = -100 µA	-4			V
$V_{CE(sat)}$*	Collector-Emitter Saturation Voltage	I_C = -100 mA I_B = -10 mA			-0.25	V
$V_{BE(on)}$*	Base-Emitter On Voltage	I_C = -100 mA V_{CE} = -1 V			-1.2	V
h_{FE}*	DC Current Gain	I_C = -10 mA V_{CE} = -1 V I_C = -100 mA V_{CE} = -1 V	50 50			
f_T	Transition Frequency	I_C = -10 mA V_{CE} = -2 V f = 100 MHz	50			MHz

* Pulsed: Pulse duration = 300 µs, duty cycle ≤ 2 %

SOT-23 MECHANICAL DATA

DIM.	mm			mils		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	0.85		1.1	33.4		43.3
B	0.65		0.95	25.6		37.4
C	1.20		1.4	47.2		55.1
D	2.80		3	110.2		118
E	0.95		1.05	37.4		41.3
F	1.9		2.05	74.8		80.7
G	2.1		2.5	82.6		98.4
H	0.38		0.48	14.9		18.8
L	0.3		0.6	11.8		23.6
M	0		0.1	0		3.9
N	0.3		0.65	11.8		25.6
O	0.09		0.17	3.5		6.7



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